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PTO/SB/50 (02-01)

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REISSUE PATENT APPLICATION TRANSMITTAL

Address to:

Assistant Commissioner for Patents
Box Reissue
Washington, DC 20231

Attorney Docket No.

57454-093

First Named Inventor

Shinichi Kobayashi

Original Patent Number

5,898,606

Original Patent Issue Date
(Month/Day/Year)

April 27, 1999

Express Mail Label No.

APPLICATION FOR REISSUE OF:

(Check applicable box)



Utility Patent



Design Patent



Plant Patent

APPLICATION ELEMENTS (37 CFR 1.173)

1. ☐ Fee Transmittal Form (PTO/SB/ 56)
(Submit an original, and a duplicate for fee processing)
2. ☐ Applicant claims small entity status. See 37 CFR 1.27.
3. ☒ Specification and Claims in double column copy of patent
format (amended, if appropriate)
4. ☒ Drawing(s) (proposed amendments, if appropriate)
5. ☐ Reissue Oath/Declaration (original or copy)
(37 C.F.R. § 1.175) (PTO/SB/51 or 52)
6. ☐ Power of Attorney
7. Original U.S. Patent currently assigned? ☒ Yes ☐ No
(If Yes, check applicable box(es))
 - ☐ Written Consent of all Assignees (PTO/SB/53)
 - ☐ 37 C.F.R. § 3.73(b) Statement
(PTO/SB/96)
8. ☐ CD-ROM or CD-R in duplicate, Computer Program (Appendix)
or large table
9. Nucleotide and/or Amino Acid Sequence Submission
(if applicable, all of the following are necessary)
 - a. ☐ Computer Readable Form (CFR)
 - b. Specification Sequence Listing on:
 - i ☐ CD-ROM (2 copies) or CD-R (2 copies); or
 - ii ☐ paper
 - c. ☐ Statements verifying identity of above copies

ACCOMPANYING APPLICATION PARTS

10. ☐ Statement of status and support for all changes
to the claims. See 37 CFR 1.173 (c).
11. ☐ Original U.S. Patent for surrender
 - ☐ Ribboned Original Patent Grant
 - ☐ Statement of Loss (PTO/SB/55)
12. ☐ Foreign Priority Claim (35 U.S.C. 119)
(if applicable)
13. ☐ Information Disclosure Statement (IDS)/PTO-1449 ☐ Copies of IDS
Citations
14. ☐ English Translation of Reissue Oath/Declaration
(if applicable)
15. ☐ Preliminary Amendment
16. ☐ Return Receipt Postcard (MPEP 503)
(Should be specifically itemized)
17. Other:

18. CORRESPONDENCE ADDRESS



Customer Number or Bar Code Label

or

☒ Correspondence address below

(Insert Customer No. or Attach bar code label here)

Name	McDermott, Will & Emery				
Address	600 13th Street, NW				
City	Washington	State	DC	Zip Code	20005
Country	USA	Telephone	(202) 756-8600	Fax	(202) 756-8087

NAME (Print/Type)

Gene Z. Robinson

Registration No. (Attorney/Agent)

33,351

Signature

Gene Z. Robinson

Date

April 27, 2001

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of :
 :
Atsushi FUKUMOTO, et al. :
 :
Serial No.: Reissue of Patent 5,898,606 : Group Art Unit: Not yet assigned
 :
Filed: April 27, 2001 : Examiner: Not yet assigned
 :
For: ELECTRICALLY PROGRAMMABLE AND ERASABLE NONVOLATILE
SEMICONDUCTOR MEMORY DEVICE AND OPERATION METHOD
THEREFOR

STATEMENT UNDER 37 CFR 1.173(C)

Commissioner for Patents
Washington, DC 20231

Sir:

Claims 1 through 11 are presented for Reissue Examination. Claims 1 and 2 are patent claims with no changes. Claims 3 through 11 are new claims added in this application. Support in the original disclosure of the 5,898,606 patent can be found as follows.

Claims 3, 5 and 10 are independent. The subject matter of these claims are illustrated in Figs. 60 and 62 of the drawings and described in detail at columns 50 and 51 of the specification. For example, the main bit line, subbit lines, first and second switching transistors, the memory cells and connections to subbit lines, and the n connection lines of claim 3 are all shown in block 1462 of Fig. 60. A local decoder is shown at 1464.

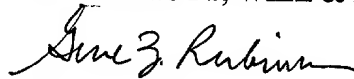
The recitation of polycrystalline silicon of claim 4 is supported by Fig. 86 and the description at column 61, lines 34-41. The recited connection lines are word lines in Fig. 60 and made of metal wiring.

Claims 5 through 9 are supported by Fig. 65 and its description at the lower portion of column 51, extending to column 52. Main bit line 92 is described as aluminum, subbit line 90 described as polycrystalline silicon. The switch 86 and memory cells 87 also are illustrated.

Claims 10 and 11 are supported by Figs. 60 and its description at columns 50 and 51 and the electron extracting features discussed, *inter alia*, at column 14, lines 27 - 45.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



Gene Z. Robinson

Registration No. 33,351

600 13th Street, N.W.
Washington, DC 20005-3096
(202) 756-8000 GZR:arp
Date: April 27, 2001
Facsimile: (202) 756-8087

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